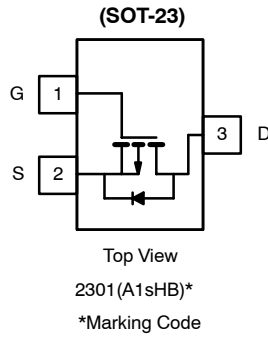


P-Channel AO2301MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
-20	0.120 @ $V_{GS} = -4.5$ V	-2.3
	0.190 @ $V_{GS} = -2.5$ V	-1.8



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	
Continuous Drain Current ( $T_J = 150^\circ\text{C}$ ) <sup>b</sup>	$I_D$	$T_A = 25^\circ\text{C}$	-2.3
		$T_A = 70^\circ\text{C}$	-1.5
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	-10	A
Continuous Source Current (Diode Conduction) <sup>b</sup>	$I_S$	-1.6	
Power Dissipation <sup>b</sup>	$P_D$	$T_A = 25^\circ\text{C}$	1.25
		$T_A = 70^\circ\text{C}$	0.8
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Maximum Junction-to-Ambient <sup>b</sup>	$R_{thJA}$	100	$^\circ\text{C/W}$
Maximum Junction-to-Ambient <sup>c</sup>		166	

- Notes
- a. Pulse width limited by maximum junction temperature.
  - b. Surface Mounted on FR4 Board,  $t \leq 5$  sec.
  - c. Surface Mounted on FR4 Board.